ANALOG DEVICES

1 pC Charge Injection, 100 pA Leakage CMOS ± 5 V/5 V/3 V 4-Channel Multiplexer

FEATURES

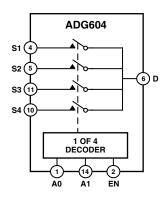
1 pC Charge Injection (Over the Full Signal Range) ±2.7 V to ±5.5 V Dual Supply 2.7 V to 5.5 V Single Supply Automotive Temperature Range: -40°C to +125°C 100 pA Max @ 25°C Leakage Currents 85 Ω Typ On Resistance Rail-to-Rail Operation Fast Switching Times Typical Power Consumption (<0.1 μ W) TTL/CMOS Compatible Inputs 14-Lead TSSOP Package

APPLICATIONS

Automatic Test Equipment Data Acquisition Systems Battery-Powered Instruments Communication Systems Sample and Hold Systems Remote-Powered Equipment Audio and Video Signal Routing Relay Replacement Avionics

FUNCTIONAL BLOCK DIAGRAM

ADG604



GENERAL DESCRIPTION

The ADG604 is a CMOS analog multiplexer, comprising four single channels. It operates from a dual supply of ± 2.7 V to ± 5.5 V, or from a single supply of 2.7 V to 5.5 V.

The ADG604 switches one of four inputs to a common output, D, as determined by the 3-bit binary address lines, A0, A1, and EN. A Logic "0" on the EN pin disables the device.

The ADG604 offers ultralow charge injection of ± 1.5 pC over the entire signal range and leakage currents of 10 pA typical at 25°C. It offers on resistance of 85 Ω typ, which is matched to within 2 Ω between channels. The ADG604 also has low power dissipation yet gives high switching speeds. The ADG604 is available in a 14-lead TSSOP package.

PRODUCT HIGHLIGHTS

- 1. Ultralow Charge Injection (Q $_{\rm INJ}:\pm1.5$ pC Typ over the Full Signal Range)
- 2. Leakage Current <0.5 nA max @ 85°C
- 3. Dual ± 2.7 V to ± 5.5 V or Single 2.7 V to 5.5 V Supply
- 4. Fully Specified to 125°C
- 5. Small 14-Lead TSSOP Package

Information furnished by Analog Devices is believed to be accurate and reliable. However, no responsibility is assumed by Analog Devices for its use, nor for any infringements of patents or other rights of third parties that may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Analog Devices.

 Www.analog.com

 Fax: 781/326-8703
 © Analog Devices, Inc., 2002

ADG604–SPECIFICATIONS

DUAL SUPPLY¹ ($V_{DD} = +5 V \pm 10\%$, $V_{SS} = -5 V \pm 10\%$, GND = 0 V. All specifications -40°C to +125°C unless otherwise noted.)

Parameter	25°C	-40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			V_{SS} to V_{DD}	V	
					$V_{DD} = +4.5 \text{ V}, V_{SS} = -4.5 \text{ V}$
On Resistance (R _{ON})	85			ΩТур	$V_{\rm S} = \pm 3 \text{ V}, \text{ I}_{\rm S} = -1 \text{ mA},$
	115	140	160	Ω Max	Test Circuit 1
On Resistance Match Between					
Channels (ΔR_{ON})	2			ΩТур	$V_{\rm S} = \pm 3 \text{ V}, I_{\rm S} = -1 \text{ mA}$
	4	5.5	6.5	Ω Max	
On-Resistance Flatness $(R_{FLAT(ON)})$	25			ΩТур	$V_{\rm S} = \pm 3 \text{ V}, \text{ I}_{\rm S} = -1 \text{ mA}$
	40	55	60	Ω Max	
LEAKAGE CURRENTS					$V_{DD} = +5.5 \text{ V}, V_{SS} = -5.5 \text{ V}$
Source OFF Leakage I _S (OFF)	±0.01			nA Typ	$V_{\rm S} = \pm 4.5 \text{ V}, V_{\rm D} = \mp 4.5 \text{ V},$
	±0.1	± 0.25	± 4	nA Max	Test Circuit 2
Drain OFF Leakage I _D (OFF)	±0.01			nA Typ	$V_{S} = \pm 4.5 V, V_{D} = \mp 4.5 V,$
	±0.1	± 0.5	± 8	nA Max	Test Circuit 2
Channel ON Leakage I _{D.} I _S (ON)	±0.01			nA Typ	$V_{S} = V_{D} = \pm 4.5 V$, Test Circuit 3
	±0.1	± 0.5	± 10	nA Max	
DICITAL INDUTS					
DIGITAL INPUTS Input High Voltage, V _{INH}			2.4	V Min	
			2.4 0.8	V Max	
Input Low Voltage, V _{INL} Input Current			0.8	v Iviax	
	0.005			μА Тур	$V_{IN} = V_{INL}$ or V_{INH}
I _{INL} or I _{INH}	0.005		± 0.1	μΑ Τyp μΑ Max	$\mathbf{v}_{\rm IN} - \mathbf{v}_{\rm INL}$ or $\mathbf{v}_{\rm INH}$
C _{IN} , Digital Input Capacitance	2		± 0.1	pF Typ	
				priyp	
DYNAMIC CHARACTERISTICS ²					
Transition Time	70			ns Typ	$V_{S1} = +3 V, V_{S4} = -3 V, R_L = 300 \Omega,$
	100	120	150	ns Max	$C_L = 35 \text{ pF}$, Test Circuit 4
t _{ON} Enable	80	100	1 = 0	ns Typ	$R_{\rm L} = 300 \ \Omega, \ C_{\rm L} = 35 \ \rm pF$
D 11	105	130	150	ns Max	$V_s = 3 V$, Test Circuit 6
t _{OFF} Enable	30		< -	ns Typ	$R_{\rm L} = 300 \ \Omega, \ C_{\rm L} = 35 \ \rm pF$
	45	55	65	ns Max	$V_s = 3 V$, Test Circuit 6
Break-Before-Make Time Delay, t_{BBM}	20		10	ns Typ	$R_L = 300 \Omega, C_L = 35 pF,$
			10	ns Min	$V_{S1} = V_{S2} = 3 V$, Test Circuit 5
Charge Injection	-1			рС Тур	$V_{\rm S} = 0$ V, $R_{\rm S} = 0$ Ω , $C_{\rm L} = 1$ nF, Test Circuit
Off Isolation	-75			dB Typ	$R_L = 50 \Omega, C_L = 5 pF, f = 10 MHz,$
Channel to Chan and Country!	70			4D T	Test Circuit 8 P = 500, C = 5 rE f = 10 MHz
Channel-to-Channel Crosstalk	-70			dB Typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 10 MHz$,
Bandwidth –3 dB	280			MH2 Tre	Test Circuit 10 $R_L = 50 \Omega$, $C_L = 5 pF$, Test Circuit 9
				MHz Typ	-
$C_{\rm S}$ (OFF)	5			pF Typ	f = 1 MHz
C_D (OFF) C_D , C_S (ON)	17 18			pF Typ pF Typ	f = 1 MHz f = 1 MHz
	10			hr. ryh	
POWER REQUIREMENTS					V_{DD} = +5.5 V, V_{SS} = -5.5 V
I _{DD}	0.001			μА Тур	Digital Inputs = $0 \text{ V or } 5.5 \text{ V}$
			1.0	µA Max	
Iss	0.001			μА Тур	Digital Inputs = $0 \text{ V or } 5.5 \text{ V}$
			1.0	µA Max	

NOTES ¹Y Version Temperature Range: -40°C to +125°C

²Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

SINGLE SUPPLY¹ ($V_{DD} = 5 V \pm 10\%$, $V_{SS} = 0 V$, GND = 0 V. All specifications -40°C to +125°C unless otherwise noted.)

Parameter	25°C	-40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			0 V to V_{DD}	v	
			e i te i DD	•	$V_{DD} = 4.5 \text{ V}, V_{SS} = 0 \text{ V}$
On Resistance (R _{ON})	210			ΩТур	$V_{\rm S} = 3.5 \text{ V}, I_{\rm S} = -1 \text{ mA},$
	290	350	380	Ω Max	Test Circuit 1
On Resistance Match Between	2,0	550	500	22 IVIUA	Test Great T
Channels (ΔR_{ON})	3			ΩТур	$V_{S} = 3.5 V, I_{S} = -1 mA$
Channels (Arton)		12	13	Ω Max	$v_{S} = 5.5 v_{3} v_{5} = 1 \text{ mm}$
		12	15	32 IVIAX	
LEAKAGE CURRENTS					$V_{DD} = 5.5 V$
Source OFF Leakage I _S (OFF)	±0.01			nA Typ	$V_{\rm S} = 1 \text{ V}/4.5 \text{ V}, V_{\rm D} = 4.5 \text{ V}/1 \text{ V},$
	±0.1	± 0.25	± 4	nA Max	Test Circuit 2
Drain OFF Leakage I _D (OFF)	±0.01			nA Typ	$V_{\rm S} = 1 \text{ V}/4.5 \text{ V}, V_{\rm D} = 4.5 \text{ V}/1 \text{ V},$
	±0.1	± 0.5	± 8	nA Max	Test Circuit 2
Channel ON Leakage I _D , I _S (ON)	±0.01	-		nA Typ	$V_{\rm S} = V_{\rm D} = 4.5 \text{ V/1 V},$
	±0.1	± 0.5	10	nA Max	Test Circuit 3
DIGITAL INPUTS					
Input High Voltage, V _{INH}			2.4	V Min	
Input Low Voltage, V _{INL}			0.8	V Max	
Input Current					
I _{INL} or I _{INH}	0.005			μА Тур	$V_{IN} = V_{INL}$ or V_{INH}
			± 0.1	µA Max	
C _{IN} , Digital Input Capacitance	2			pF Typ	
DYNAMIC CHARACTERISTICS ²					
	00				V = 2 V V = 0 V P = 200 O
Transition Time	90	105	210	ns Typ	$V_{S1} = 3 V, V_{S4} = 0 V, R_L = 300 \Omega,$
	150	185	210	ns Max	$C_L = 35 \text{ pF}$, Test Circuit 4
t _{ON} Enable	105			ns Typ	$R_L = 300 \Omega$, $C_L = 35 pF$
	150	190	220	ns Max	$V_s = 3 V$, Test Circuit 6
t _{OFF} Enable	45			ns Typ	$R_L = 300 \Omega, C_L = 35 pF$
	70	80	90	ns Max	$V_s = 3 V$, Test Circuit 6
Break-Before-Make Time Delay, t _{BBM}	30			ns Typ	$R_L = 300 \Omega$, $C_L = 35 pF$,
			10	ns Min	$V_{S1} = V_{S2} = 3 V$, Test Circuit 5
Charge Injection	0.3			рС Тур	$V_{S} = 0 V$, $R_{S} = 0 \Omega$, $C_{L} = 1 nF$,
					Test Circuit 7
Off Isolation	-65			dB Typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 10 MHz$,
					Test Circuit 8
Channel-to-Channel Crosstalk	-70			dB Typ	$R_L = 50 \Omega, C_L = 5 pF, f = 10 MHz,$
					Test Circuit 10
Bandwidth –3 dB	250			MHz Typ	$R_L = 50 \Omega$, $C_L = 5 pF$, Test Circuit 9
C_{s} (OFF)	5			pF Typ	f = 1 MHz
$C_{\rm S}(\rm OFF)$ $C_{\rm D}(\rm OFF)$	17			pF Typ pF Typ	f = 1 MHz
	17				f = 1 MHz
$C_D, C_S(ON)$	10			pF Typ	
POWER REQUIREMENTS					V_{DD} = 5.5 V
					Digital Inputs = 0 V or 5.5 V
I _{DD}	0.001			μА Тур	
			1.0	µA Max	

NOTES

¹Y Version Temperature Range: -40°C to +125°C ²Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

ADG604–SPECIFICATIONS

SINGLE SUPPLY¹ ($V_{DD} = 3 V \pm 10\%$, $V_{SS} = 0 V$, GND = 0 V. All specifications -40°C to +125°C unless otherwise noted.)

Parameter	25°C	-40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			0 V to V_{DD}	v	
On Resistance (R _{ON})	380	420	460	ΩТур	$V_{DD} = 2.7 V, V_{SS} = 0 V$ $V_S = 1.5 V, I_S = -1 mA,$ Test Circuit 1
On Resistance Match Between Channels (ΔR_{ON})			5	ΩТур	$V_{\rm S} = 1.5 \text{ V}, \text{ I}_{\rm S} = -1 \text{ mA}$
LEAKAGE CURRENTS Source OFF Leakage I _S (OFF)	$\pm 0.01 \\ \pm 0.1$	±0.25	±4	nA Typ nA Max	$V_{DD} = 3.3 V$ $V_{S} = 1 V/3 V$, $V_{D} = 3 V/1 V$, Test Circuit 2
Drain OFF Leakage I_D (OFF)	$\pm 0.01 \\ \pm 0.1$	±0.5	±8	nA Typ nA Max	$V_S = 1 V/3 V$, $V_D = 3 V/1 V$, Test Circuit 2
Channel ON Leakage I_D , I_S (ON)	$\pm 0.01 \\ \pm 0.1$	±0.5	±10	nA Typ nA Max	$V_{\rm S} = V_{\rm D} = 1 \text{ V/3 V},$ Test Circuit 3
DIGITAL INPUTS Input High Voltage, V _{INH} Input Low Voltage, V _{INL}			2.0 0.8	V Min V Max	
Input Current I _{INL} or I _{INH}	0.005		±0.1	μΑ Typ μΑ Max	$V_{IN} = V_{INL}$ or V_{INH}
C _{IN} , Digital Input Capacitance	2			pF Typ	
DYNAMIC CHARACTERISTICS ²					
Transition Time	170 320	390	450	ns Typ ns Max	$V_{S1} = 2 V, V_{S4} = 0 V, R_L = 300 \Omega,$ $C_L = 35 pF, Test Circuit 4$
t _{ON} Enable	180 250	265	390	ns Typ ns Max	$R_L = 300 \Omega$, $C_L = 35 pF$ $V_S = 2 V$, Test Circuit 6
t _{OFF} Enable	100 160	205	225	ns Typ ns Max	$R_L = 300 \Omega$, $C_L = 35 pF$ $V_S = 2 V$, Test Circuit 6
Break-Before-Make Time Delay, t_{BBM}	100		10	ns Typ ns Min	$R_L = 300 \Omega, C_L = 35 pF,$ $V_{S1} = V_{S2} = 2 V,$ Test Circuit 5
Charge Injection	0.3		10	рС Тур	$V_{s} = 0 V \text{ to } 3.3 V, R_{s} = 0 \Omega, C_{L} = 1 \mu\text{F},$ Test Circuit 7
Off Isolation	-65			dB Typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 10 MHz$, Test Circuit 8
Channel-to-Channel Crosstalk	70			dB Typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 10 MHz$, Test Circuit 10
Bandwidth -3 dB $C_{S} (OFF)$ $C_{D} (OFF)$ $C_{D}, C_{S} (ON)$	250 5 17 18			MHz Typ pF Typ pF Typ pF Typ	$R_{L} = 50 \Omega, C_{L} = 5 \text{ pF}, \text{ Test Circuit 9}$ f = 1 MHz f = 1 MHz f = 1 MHz
POWER REQUIREMENTS					$V_{DD} = 3.3 V$
I _{DD}	0.001		1.0	µА Тур µА Мах	Digital Inputs = 0 V or 3.3 V

NOTES ¹Y Version Temperature Range: -40°C to +125°C

²Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

ABSOLUTE MAXIMUM RATINGS¹

(h
V_{DD} to V_{SS}
V_{DD} to GND $\hdots0.3$ V to +6.5 V
V _{SS} to GND
Analog Inputs ² V_{SS} –0.3 V to V_{DD} + 0.3 V
Digital Inputs ² -0.3 V to V _{DD} + 0.3 V or
30 mA, Whichever Occurs First
Peak Current, S or D 20 mA
(Pulsed at 1 ms, 10% Duty Cycle Max)
Continuous Current, S or D 10 mA
Operating Temperature Range
Automotive (Y Version) $\dots -40^{\circ}$ C to $+125^{\circ}$ C
Storage Temperature Range65°C to +150°C

Junction Temperature 150°C
TSSOP Package
θ_{IA} Thermal Impedance 150°C/W
$\theta_{\rm IC}$ Thermal Impedance
Lead Temperature, Soldering (10 seconds) 300°C
IR Reflow, Peak Temperature 220°C

NOTES

¹Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Only one absolute maximum rating may be applied at any one time.

²Overvoltages at EN, A0, A1, S, or D will be clamped by internal diodes. Current should be limited to the maximum ratings given.

ORDERING GUIDE

Model Option	Temperature Range	Package Description	Package
ADG604YRU	–40°C to +125°C	Thin Shrink Small Outline (TSSOP)	RU-14

PIN CONFIGURATION

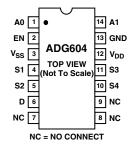


Table I. Truth Table

A1	A0	EN	ON Switch
Х	X	0	None
0	0	1	1
0	1	1	2
1	0	1	3
1	1	1	4

CAUTION_

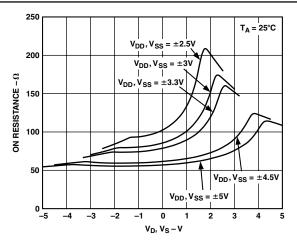
ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the ADG604 features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high-energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



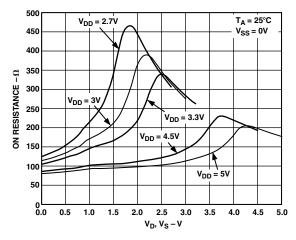
TERMINOLOGY

V _{DD}	Most Positive Power Supply Potential
V _{SS}	Most Negative Power Supply in a Dual Supply Application. In single supply applications, this should be tied to
	ground at the device.
GND	Ground (0 V) Reference
I _{DD}	Positive Supply Current
I _{SS}	Negative Supply Current
S	Source Terminal. May be an input or output.
D	Drain Terminal. May be an input or output.
R _{ON}	Ohmic Resistance between D and S
ΔR_{ON}	On Resistance Match between any two channels, i.e., R _{ON} Max – R _{ON} Min
R _{FLAT(ON)}	Flatness is defined as the difference between the maximum and minimum value of On resistance as measured
	over the specified analog signal range.
I _S (OFF)	Source Leakage Current with the Switch "OFF"
I _D (OFF)	Drain Leakage Current with the Switch "OFF"
$I_D, I_S (ON)$	Channel Leakage Current with the Switch "ON"
V_D, V_S	Analog Voltage on Terminals D, S
V _{INL}	Maximum Input Voltage for Logic "0"
V_{INH}	Minimum Input Voltage for Logic "1"
$\mathbf{I}_{\mathrm{INL}}~(\mathbf{I}_{\mathrm{INH}})$	Input Current of the Digital Input
C _S (OFF)	Channel Input Capacitance for "OFF" Condition
C _D (OFF)	Channel Output Capacitance for "OFF" Condition
$C_D, C_S (ON)$	"On" Switch Capacitance
C _{IN}	Digital Input Capacitance
t _{ON} (EN)	Delay time between the 50% and 90% points of the digital input and switch "ON" condition.
t _{OFF} (EN)	Delay time between the 50% and 90% points of the digital input and switch "OFF" condition.
t _{TRANSITION}	Delay time between the 50% and 90% points of the digital input and switch "ON" condition when switching
	from one address state to another.
t _{BBM}	"OFF" time or "ON" time measured between the 80% points of both switches, when switching from one address
	state to another.
Charge Injection	A measure of the glitch impulse transferred from the digital input to the analog output during switching.
Crosstalk	A measure of unwanted signal that is coupled through from one channel to another as a result of parasitic capacitance.
Off Isolation	A measure of unwanted signal coupling through an "On" switch.
Bandwidth	Frequency Response of the "On" Switch
Insertion Loss	Loss Due to the On Resistance of the Switch
Bandwidth	A measure of unwanted signal coupling through an "On" switch. Frequency Response of the "On" Switch

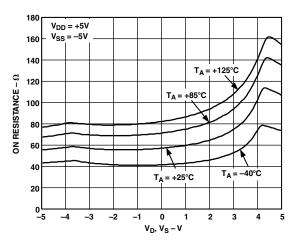
Typical Performance Characteristics-ADG604



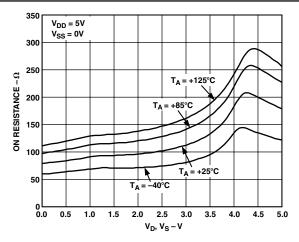
TPC 1. On Resistance vs. V_D (V_S), Dual Supply



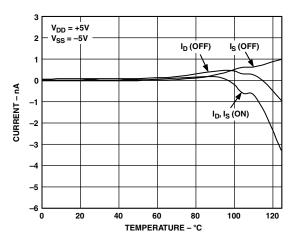
TPC 2. On Resistance vs. V_D (V_S), Single Supply



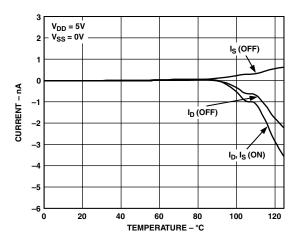
TPC 3. On Resistance vs. V_D (V_S) for Different Temperatures, Dual Supply



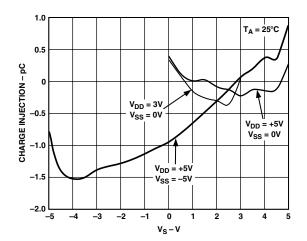
TPC 4. On Resistance vs. V_D (V_S) for Different Temperatures, Single Supply



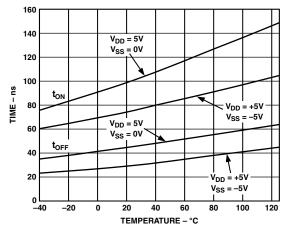
TPC 5. Leakage Currents vs. Temperature, Dual Supply



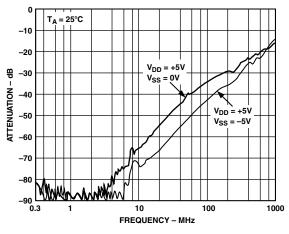
TPC 6. Leakage Currents vs. Temperature, Single Supply



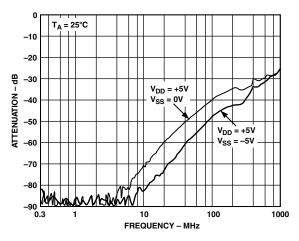
TPC 7. Charge Injection vs. Source Voltage



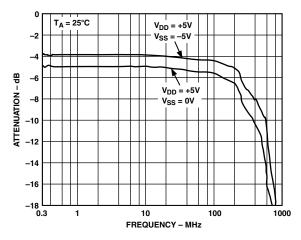
TPC 8. t_{ON}/t_{OFF} Times vs. Temperature



TPC 9. Off Isolation vs. Frequency



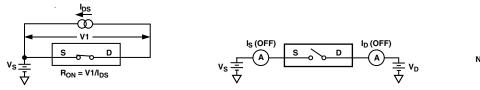
TPC 10. Crosstalk vs. Frequency



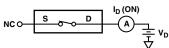
TPC 11. On Response vs. Frequency

REV.0

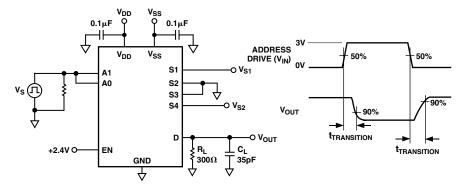
Test Circuits



Test Circuit 1. On Resistance

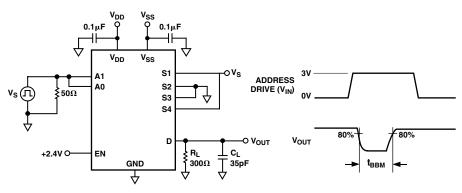


Test Circuit 3. On Leakage

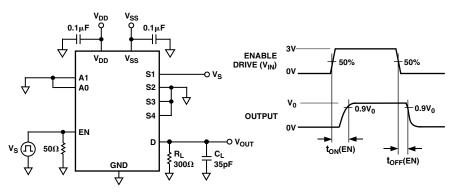


Test Circuit 2. Off Leakage

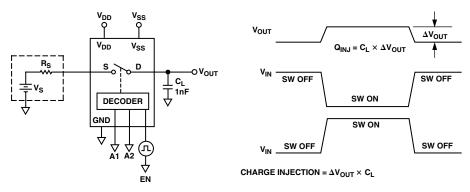
Test Circuit 4. Switching Time of Multiplexer, t_{TRANSITION}



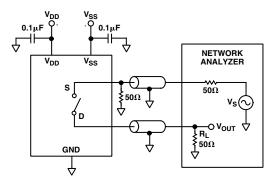
Test Circuit 5. Break-Before-Make Delay, t_{BBM}

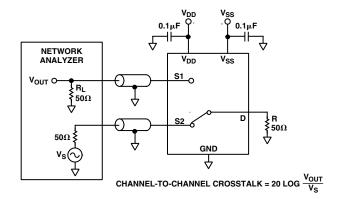


Test Circuit 6. Enable Delay, t_{ON} (EN), t_{OFF} (EN)



Test Circuit 7. Charge Injection

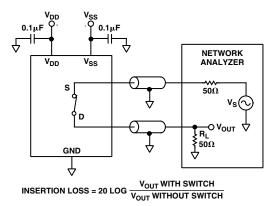




OFF ISOLATION = 20 LOG $\frac{V_{OUT}}{V_S}$

Test Circuit 8. Off Isolation

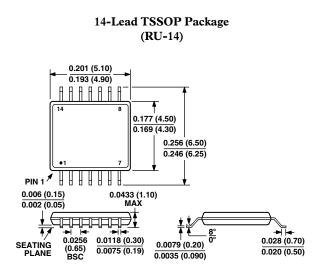
Test Circuit 10. Channel-to-Channel Crosstalk



Test Circuit 9. Bandwidth

OUTLINE DIMENSIONS

Dimensions shown in inches and (mm).



C02752-0-2/02(0)

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Analog Devices Inc.: ADG604YRUZ ADG604YRUZ-REEL7